

IPP70N04S307AKSA1

IPP70N04S307AKSA1 Information



For Reference Only

Part Number IPP70N04S307AKSA1
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 40V 80A TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPP70N04S307AKSA1 Specifications

| Manufacturer Part Number IPP70N04S307AKSA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 50µA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | | |
|---|--|--------------------------------------|
| Category Discrete Semiconductor Products Package TO-220-3 Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 50μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Manufacturer Part Number | IPP70N04S307AKSA1 |
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| Series OptiMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 40V Current - Continuous Drain (Id) @ 25°C 80A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 50μA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | | Transistors - FETs, MOSFETs - Single |
| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 50μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 70A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3 | Package | TO-220-3 |
| Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C BoA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO220-3-1 Package / Case MOSFET (Metal Oxide) MOSFET (Metal Oxide) 40V 60V 60V 80A (Tc) 80A | Series | OptiMOS? |
| Drain to Source Voltage (Vdss)40VCurrent - Continuous Drain (Id) @ 25°C80A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 50μAGate Charge (Qg) (Max) @ Vgs40nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2700pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 70A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3 | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature Supplier Device Package PG-TO220-3-1 Package / Case 80A (Tc) 80A | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO220-3-1 Package / Case Ann. 4V @ 50μA 4V @ 50μA 40nC @ 10V 2700pF @ 25V ±20V FET Feature - - - - - - - - - - - - - | Drain to Source Voltage (Vdss) | 40V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package PG-TO220-3 40nC @ 10V 2700pF @ 25V +20V +20V FET Feature - 6.5 mOhm @ 70A, 10V Through Hole Supplier Device Package PG-TO220-3-1 TO-220-3 | Current - Continuous Drain (Id) @ 25°C | 80A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2700pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Drive Voltage (Max Rds On, Min Rds On) | 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Vgs(th) (Max) @ Id | 4V @ 50μA |
| Vgs (Max)±20VFET Feature-Power Dissipation (Max)79W (Tc)Rds On (Max) @ Id, Vgs6.5 mOhm @ 70A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3 | Gate Charge (Qg) (Max) @ Vgs | 40nC @ 10V |
| FET Feature - Power Dissipation (Max) 79W (Tc) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Input Capacitance (Ciss) (Max) @ Vds | 2700pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 6.5 mOhm @ 70A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Vgs (Max) | ±20V |
| Rds On (Max) @ Id, Vgs6.5 mOhm @ 70A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3-1Package / CaseTO-220-3 | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Power Dissipation (Max) | 79W (Tc) |
| Mounting Type Through Hole Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Rds On (Max) @ Id, Vgs | 6.5 mOhm @ 70A, 10V |
| Supplier Device Package PG-TO220-3-1 Package / Case TO-220-3 | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-220-3 | Mounting Type | Through Hole |
| | Supplier Device Package | PG-TO220-3-1 |
| Report errors? | Package / Case | TO-220-3 |
| | | Report errors? |

IPP70N04S307AKSA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPP70N04S307AKSA1 Payment Methods



















IPP70N04S307AKSA1 Shipping Methods













If you have any question about IPP70N04S307AKSA1, please do not hesitate to contact us!

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